

1. Scope :

This specification applies to P/N silicon TVS diode chips,
Device NO. SD-113B6

2. Structure :

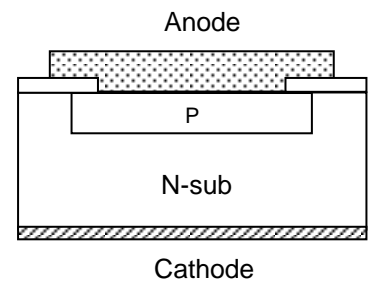
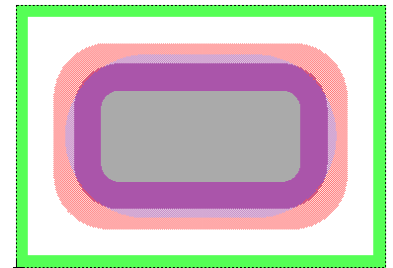
- 2-1. Planar type : P/N Diode.
- 2-2. Electrodes :
Top side : Aluminum alloy.
Back side : Gold layer.

3. Size :

- 3-1. Chip size : 15.4 mils x 10.6 mils (0.390 mm x 0.270 mm).
- 3-2. Chip thickness : 5.9 ± 1.0 mils (0.150 ± 0.0254 mm)
- 3-3. Bonding pad : 10.6 mils x 5.9 mils (0.270 mm x 0.150 mm).
- 3-4. Pattern drawing : Refer to the attached drawing.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Reverse Working Voltage	V _{RWM}			29	V	-
Reverse Current	I _R			600	nA	V _R =29V E _e =0mW/cm ²
Reverse Breakdown Voltage	V _(BR)	34	36	38	V	I _R =5mA E _e =0mW/cm ²
Capacitance	C		21		pF	F=1MHZ, V _R =0V
Reverse Clamping Voltage <i>*IEC61000-4-5 Standard.</i>	V _C		41.8		V	IPP=1A Tp=8/20us
			66.8		V	IPP=2.8A Tp=8/20us
Forward Voltage	V _f			1.2	V	I _F =10mA E _e =0mW/cm ²



Parameter	Symbol	Rating	Unit
ESD Voltage Air <i>*IEC61000-4-2 Standard.</i>	V _{ESD}	30	KV
ESD Voltage Contact <i>*IEC61000-4-2 Standard.</i>		20	

*AEC-Q101 qualified.